



MMBTH24

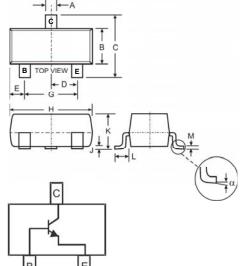
NPN SURFACE MOUNT VHF/UHF TRANSISTOR

Features

- Designed for VHF/UHF Amplifier Applications and High Output VHF Oscillators
- High Current Gain Bandwidth Product
- Ideal for Mixer and RF Amplifier Applications with collector currents in the 100µA - 30 mA Range
- Lead Free/RoHS Compliant (Note 3)

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



SOT-23									
Dim	Min	Max							
Α	0.37	0.51							
В	1.20	1.40 2.50							
С	2.30								
D	0.89	1.03 0.60							
Е	0.45								
G	1.78	2.05 3.00 0.10 1.10							
Н	2.80								
J	0.013								
K	0.903								
L	0.45	0.61							
М	0.085	0.180							
α	0°	8°							
All Dimensions in mm									

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
Collector-Base Voltage	V_{CBO}	40	V		
Collector-Emitter Voltage	$V_{\sf CEO}$	40	V		
Emitter-Base Voltage	V_{EBO}	4.0	V		
Collector Current - Continuous (Note 1)	I _C	50	mA		
Power Dissipation (Note 1)	P _d	300	mW		
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	417	°C/W		
Operating and Storage Temperature Range	T_{j}, T_{STG}	-55 to +150	°C		

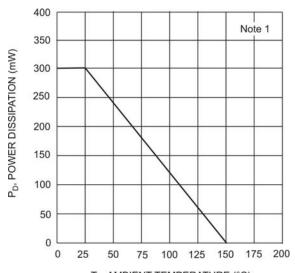
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)	<u> </u>		•	•	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40	_	V	$I_{C} = 1 \text{mA}, I_{B} = 0$
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	40	_	V	$I_C = 100 \mu A, I_E = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	4.0	_	V	$I_E = 10 \mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	100	nA	$V_{CB} = 30V, I_{E} = 0$
Emitter Cutoff Current	I _{EBO}	_	100	nA	$V_{EB} = 2V$, $I_C = 0$
ON CHARACTERISTICS (Note 2)					
DC Current Gain	h _{FE}	30	_	_	$I_{C} = 8mA, V_{CE} = 10.0V$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.5	V	$I_C = 4mA, I_B = 400\mu A$
Base-Emitter On Voltage	V _{BE(SAT)}	_	0.95	V	$I_{C} = 4mA, V_{CE} = 10.0V$
SMALL SIGNAL CHARACTERISTICS			•	•	
Current Gain-Bandwidth Product	f _T	400	_	MHz	$V_{CE} = 10V, f = 100MHz, I_{C} = 8mA$
Collector-Base Capacitance	С _{СВ}	_	0.7	pF	$V_{CB} = 10V, f = 1.0MHz, I_E = 0$
Collector-Base Feedback Capacitance	C_{RB}	_	0.65	pF	$V_{CB} = 10V, f = 1.0MHz, I_E = 0$
Collector-Base Time Constant	Rb'Cc	_	9	ps	I _C = 4mA, V _{CB} = 10V, f = 31.8MHz

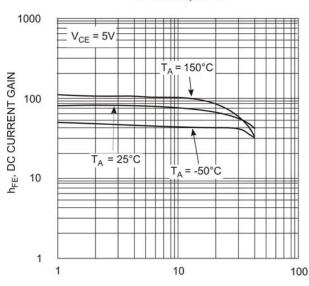
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch pad layout, as shown on Diodes Inc. suggested pad layout Notes: document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

- Short duration pulse test used to minimize self-heating effect.
- No purposefully added lead.

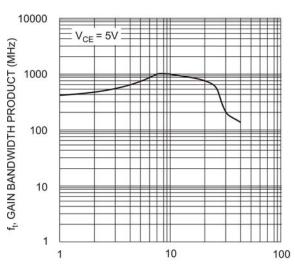




T_A, AMBIENT TEMPERATURE (°C) Fig. 1, Max Power Dissipation vs Ambient Temperature



I_C, COLLECTOR CURRENT (mA) Fig. 3, DC Current Gain vs. Collector Current



I_C, COLLECTOR CURRENT (mA)
Fig. 5, Gain Bandwidth Product vs Collector Current

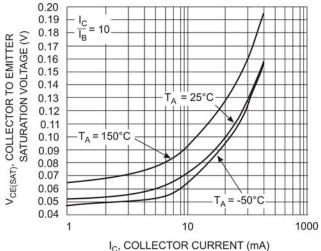


Fig. 2 Collector Emitter Saturation Voltage vs. Collector Current

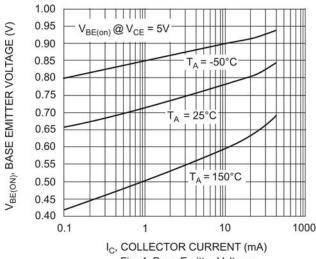


Fig. 4 Base Emitter Voltage vs. Collector Current

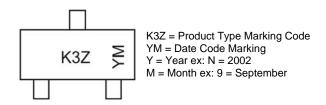


Ordering Information (Note 4)

Device	Packaging	Shipping			
MMBTH24-7-F	SOT-23	3000/Tape & Reel			

Notes: 4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Х	Υ	Z
Month	Jan	Fe	b I	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t I	VoV	Dec
Code	1	2		3	4	5	6		7	8	9	0		N	D

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